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(54) **SEMICONDUCTOR DEVICES INCLUDING
PROTRUDING INSULATION PORTIONS
BETWEEN ACTIVE FINS**

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(57) **ABSTRACT**

A semiconductor device can include a field insulation layer including a planar major surface extending in first and second orthogonal directions and a protruding portion that protrudes a particular distance from the major surface relative to the first and second orthogonal directions. First and second multi-channel active fins can extend on the field insulation layer, and can be separated from one another by the protruding portion. A conductive layer can extend from an uppermost surface of the protruding portion to cross over the protruding portion between the first and second multi-channel active fins.

